

LOW NOISE AMPLIFIER

Features

- Low noise
- High intercept
- Active Bias
- Internal voltage regulator
- Unconditionally stable

Options

- Other bandwidths
- Gain levels
- Lower noise figure
- Higher Ip3
- Other mechanical configurations



PS725701

Description

Designed for front end use in the UHF band, these amplifiers utilize GaAs FET devices to achieve low noise and high third order intercept performance, ideal for Paging, Mobile, and WLL. The unit contains an internal voltage regulator and active bias.



Model	PS725701	Units
Frequency	30-515	MHz
Gain (min)	22	dB
Flatness (max)	+/-0.8	dB
NF (max)	4.0	dB
Input Return Loss (min)	12	dB
Output Return Loss (min)	14	dB
P1dB (min)	+23	dBm
Input Ip3 (min)	+11	dBm
DC Current (max)	220	mA

Specifications at T = +25°C and VDC = +15V

Storage temperature: -40 to +85°C

Humidity: 95% relative

Input/Output impedance: 50 Ω

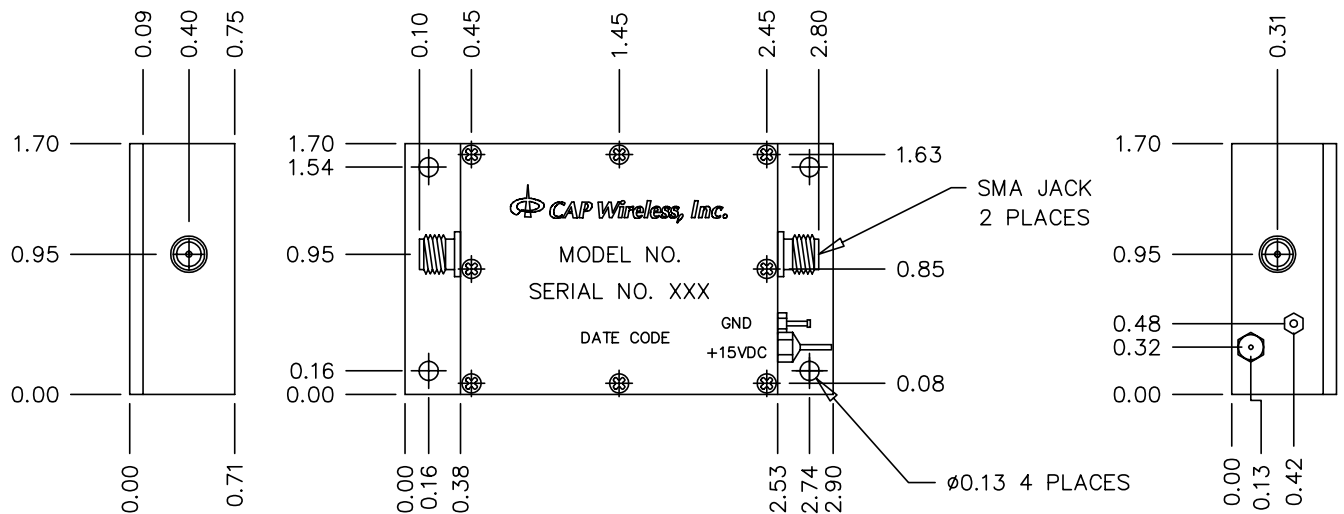
Input/Output: SMA



LOW NOISE AMPLIFIER

PS725701

Outline Drawing D



Company Design Philosophy

Essential to the company's strategy is the use of the latest and most sophisticated design software available. These design tools include complete suites of Agilent-EEsof, and AWR- Microwave Office, circuit and system high frequency EDA tools. The company consistently achieves its goal of accurately creating "prototypes" in software, as evidenced by its ability to go directly from a simulated design to deliverable prototypes and rapidly ramp to fulfill volume requirements. A crucial element of the company's development philosophy is to "design for production" to drastically improve manufacturability by virtually eliminating tuning and adjustments as part of the manufacturing process. The result is lower cost, higher reliability products with predictable delivery times.

The products shown on these data sheets are merely a representation of the company's capabilities, where a library of designs is available to draw upon to meet specific customer performance requirements. If you have a unique requirement, contact the factory to explore the latest in technology.